

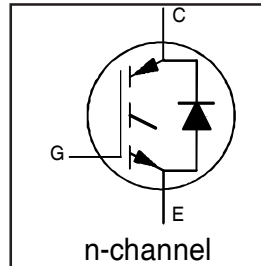
# IRG4BC10SD

INSULATED GATE BIPOLAR TRANSISTOR WITH  
ULTRAFAST SOFT RECOVERY DIODE

Standard Speed CoPack  
IGBT

### Features

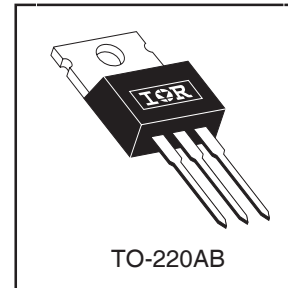
- Extremely low voltage drop 1.1Vtyp. @ 2A
- S-Series: Minimizes power dissipation at up to 3 KHz PWM frequency in inverter drives, up to 4 KHz in brushless DC drives.
- Very Tight Vce(on) distribution
- IGBT co-packaged with HEXFRED™ ultrafast, ultra-soft-recovery anti-parallel diodes for use in bridge configurations
- Industry standard TO-220AB package



$V_{CES} = 600V$
$V_{CE(on)} \text{ typ.} = 1.10V$
@ $V_{GE} = 15V, I_C = 2.0A$

### Benefits

- Generation 4 IGBTs offer highest efficiencies available
- IGBTs optimized for specific application conditions
- HEXFRED diodes optimized for performance with IGBTs . Minimized recovery characteristics require less/no snubbing
- Lower losses than MOSFET's conduction and Diode losses



### Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	14	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	8.0	
$I_{CM}$	Pulsed Collector Current ①	18	
$I_{LM}$	Clamped Inductive Load Current ②	18	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	4.0	
$I_{FM}$	Diode Maximum Forward Current	18	
$V_{GE}$	Gate-to-Emitter Voltage	$\pm 20$	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	38	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	15	
$T_J$	Operating Junction and	-55 to +150	$^\circ C$
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

### Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	—	3.3	$^\circ C/W$
$R_{\theta JC}$	Junction-to-Case - Diode	—	—	7.0	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	80	
Wt	Weight	—	2.0(0.07)	—	g (oz)

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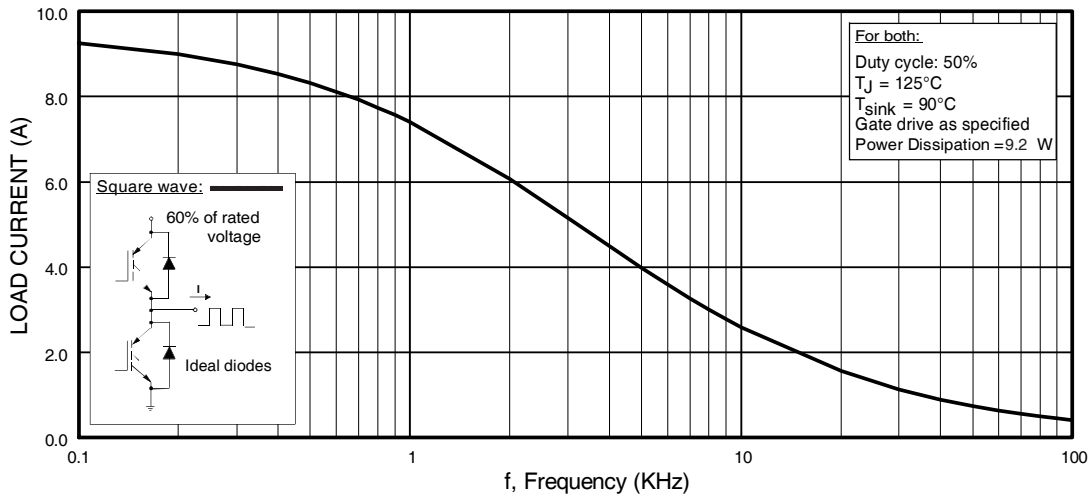
## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)CES</sub>	Collector-to-Emitter Breakdown Voltage <sup>③</sup>	600	—	—	V	V <sub>GE</sub> = 0V, I <sub>C</sub> = 250μA
ΔV <sub>(BR)CES</sub> /ΔT <sub>J</sub>	Temperature Coeff. of Breakdown Voltage	—	0.64	—	V/°C	V <sub>GE</sub> = 0V, I <sub>C</sub> = 1.0mA
V <sub>CE(on)</sub>	Collector-to-Emitter Saturation Voltage	—	1.58	1.8	V	I <sub>C</sub> = 8.0A I <sub>C</sub> = 14.0A I <sub>C</sub> = 8.0A, T <sub>J</sub> = 150°C
		—	2.05	—		
		—	1.68	—		
V <sub>GE(th)</sub>	Gate Threshold Voltage	3.0	—	6.0		V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 250μA
ΔV <sub>GE(th)</sub> /ΔT <sub>J</sub>	Temperature Coeff. of Threshold Voltage	—	-9.5	—	mV/°C	V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 250μA
g <sub>fe</sub>	Forward Transconductance <sup>④</sup>	3.65	5.48	—	S	V <sub>CE</sub> = 100V, I <sub>C</sub> = 8.0A
I <sub>CES</sub>	Zero Gate Voltage Collector Current	—	—	250	μA	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 600V V <sub>GE</sub> = 0V, V <sub>CE</sub> = 600V, T <sub>J</sub> = 150°C
		—	—	1000		
V <sub>FM</sub>	Diode Forward Voltage Drop	—	1.5	1.8	V	I <sub>C</sub> = 4.0A I <sub>C</sub> = 4.0A, T <sub>J</sub> = 150°C
		—	1.4	1.7		
I <sub>GES</sub>	Gate-to-Emitter Leakage Current	—	—	±100	nA	V <sub>GE</sub> = ±20V

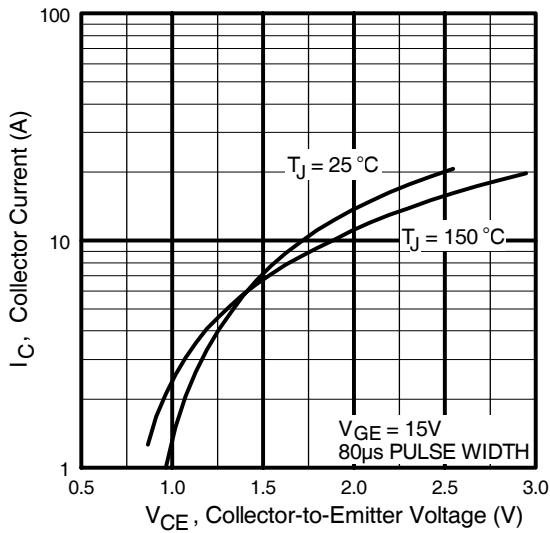
## Switching Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q <sub>g</sub>	Total Gate Charge (turn-on)	—	15	22	nC	I <sub>C</sub> = 8.0A V <sub>CC</sub> = 400V V <sub>GE</sub> = 15V See Fig. 8
Q <sub>ge</sub>	Gate - Emitter Charge (turn-on)	—	2.42	3.6		
Q <sub>gc</sub>	Gate - Collector Charge (turn-on)	—	6.53	9.8		
t <sub>d(on)</sub>	Turn-On Delay Time	—	76	—	ns	T <sub>J</sub> = 25°C I <sub>C</sub> = 8.0A, V <sub>CC</sub> = 480V V <sub>GE</sub> = 15V, R <sub>G</sub> = 100Ω Energy losses include "tail" and diode reverse recovery. See Fig. 9, 10, 18
t <sub>r</sub>	Rise Time	—	32	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	815	1200		
t <sub>f</sub>	Fall Time	—	720	1080		
E <sub>on</sub>	Turn-On Switching Loss	—	0.31	—		
E <sub>off</sub>	Turn-Off Switching Loss	—	3.28	—	mJ	
E <sub>ts</sub>	Total Switching Loss	—	3.60	10.9		
E <sub>ts</sub>	Total Switching Loss	—	1.46	2.6	mJ	I <sub>C</sub> = 5.0A
t <sub>d(on)</sub>	Turn-On Delay Time	—	70	—	ns	T <sub>J</sub> = 150°C, See Fig. 10,11, 18 I <sub>C</sub> = 8.0A, V <sub>CC</sub> = 480V V <sub>GE</sub> = 15V, R <sub>G</sub> = 100Ω Energy losses include "tail" and diode reverse recovery.
t <sub>r</sub>	Rise Time	—	36	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	890	—		
t <sub>f</sub>	Fall Time	—	890	—		
E <sub>ts</sub>	Total Switching Loss	—	3.83	—	mJ	
L <sub>E</sub>	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
C <sub>ies</sub>	Input Capacitance	—	280	—	pF	V <sub>GE</sub> = 0V V <sub>CC</sub> = 30V f = 1.0MHz See Fig. 7
C <sub>oes</sub>	Output Capacitance	—	30	—		
C <sub>res</sub>	Reverse Transfer Capacitance	—	4.0	—		
t <sub>rr</sub>	Diode Reverse Recovery Time	—	28	42	ns	T <sub>J</sub> = 25°C See Fig. 14 T <sub>J</sub> = 125°C
		—	38	57		
I <sub>rr</sub>	Diode Peak Reverse Recovery Current	—	2.9	5.2	A	T <sub>J</sub> = 25°C See Fig. 15 T <sub>J</sub> = 125°C
		—	3.7	6.7		
Q <sub>rr</sub>	Diode Reverse Recovery Charge	—	40	60	nC	T <sub>J</sub> = 25°C See Fig. 16 T <sub>J</sub> = 125°C
		—	70	105		
di <sub>(rec)</sub> M/dt	Diode Peak Rate of Fall of Recovery During t <sub>b</sub>	—	280	—	A/μs	T <sub>J</sub> = 25°C See Fig. 17 T <sub>J</sub> = 125°C
		—	235	—		

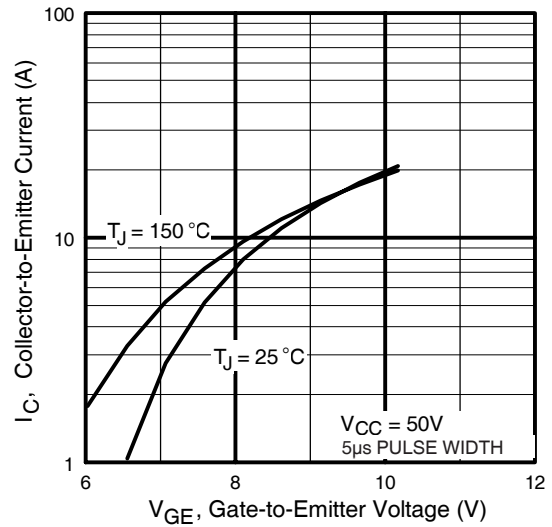
Details of note ① through ④ are on the last page



**Fig. 1 - Typical Load Current vs. Frequency**  
 (Load Current =  $I_{\text{RMS}}$  of fundamental)

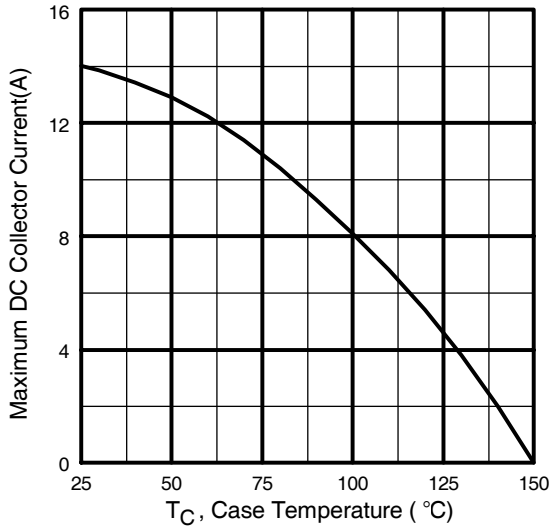


**Fig. 2 - Typical Output Characteristics**

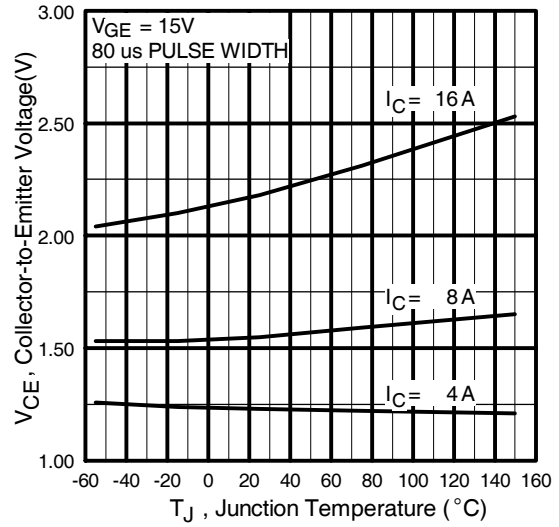


**Fig. 3 - Typical Transfer Characteristics**

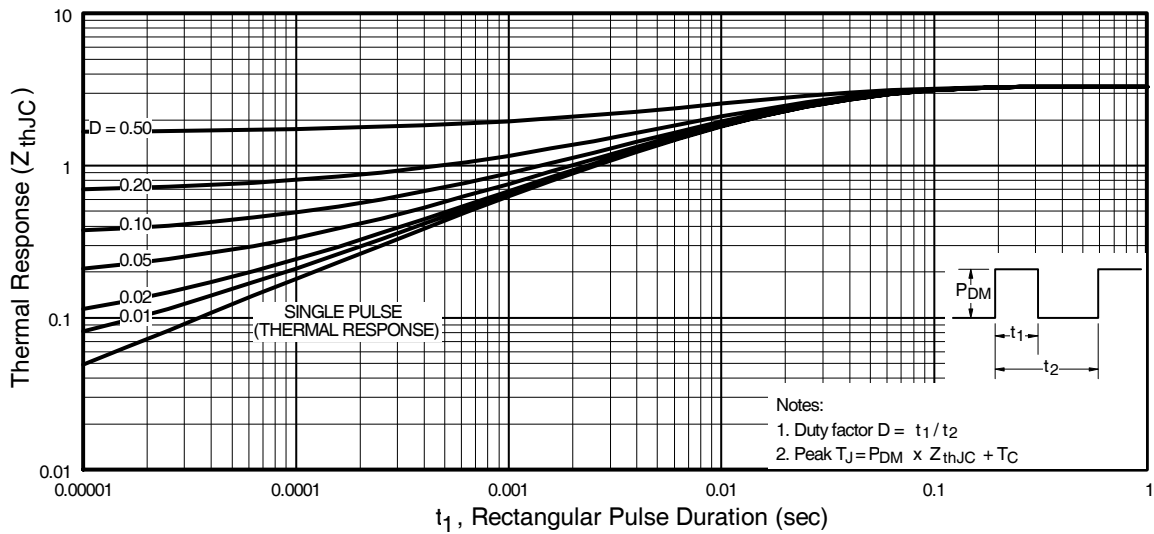
# IRG4BC10SD



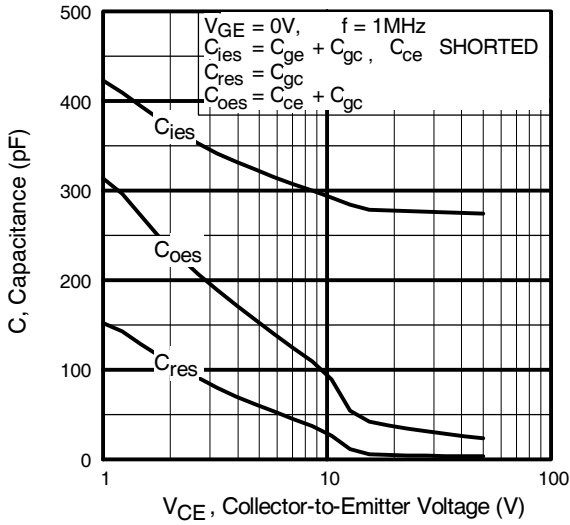
**Fig. 4** - Maximum Collector Current vs. Case Temperature



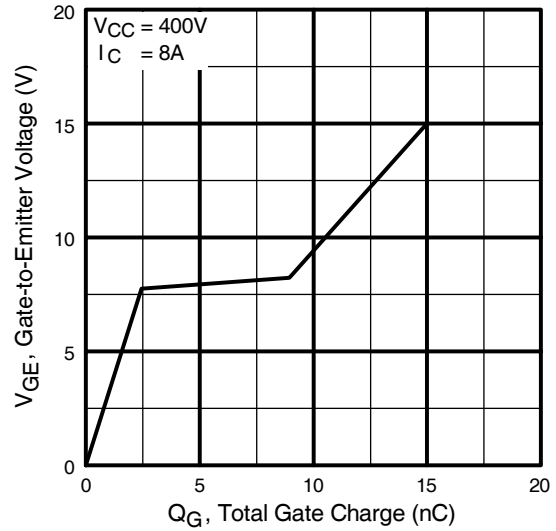
**Fig. 5** - Typical Collector-to-Emitter Voltage vs. Junction Temperature



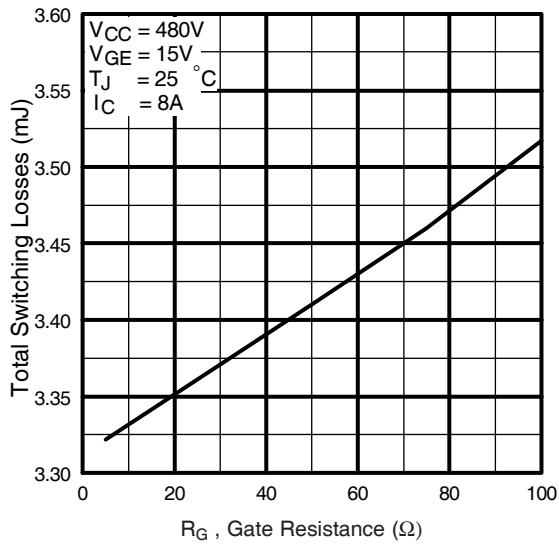
**Fig. 6** - Maximum Effective Transient Thermal Impedance, Junction-to-Case



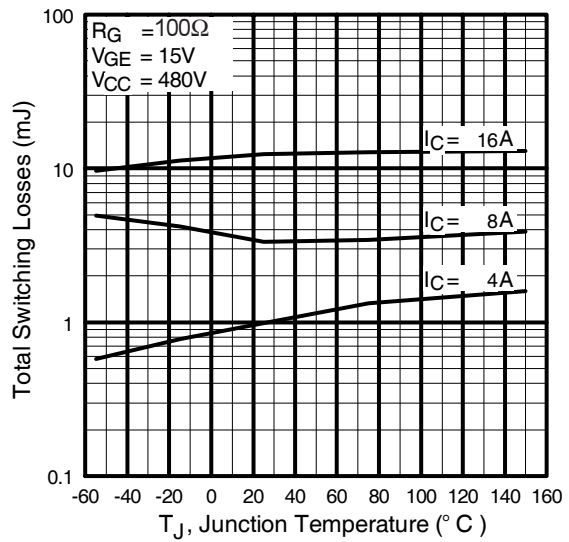
**Fig. 7** - Typical Capacitance vs. Collector-to-Emitter Voltage



**Fig. 8** - Typical Gate Charge vs. Gate-to-Emitter Voltage

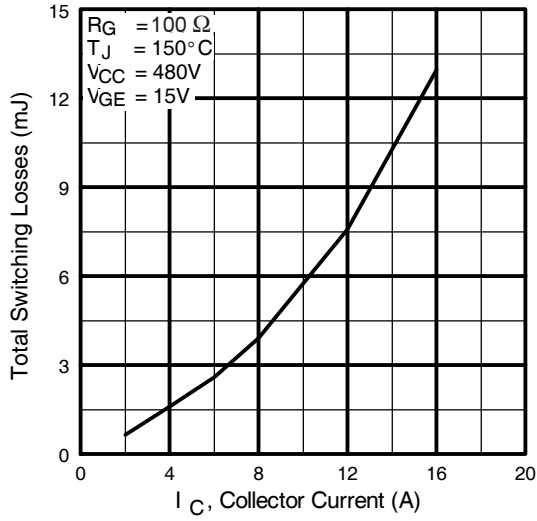


**Fig. 9** - Typical Switching Losses vs. Gate Resistance

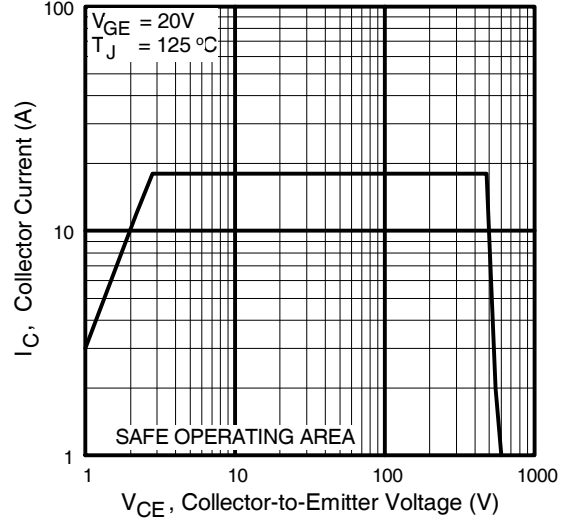


**Fig. 10** - Typical Switching Losses vs. Junction Temperature

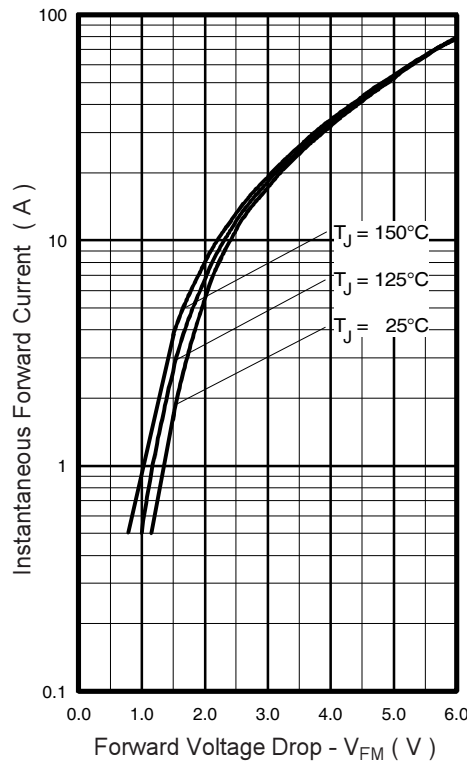
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**Fig. 11** - Typical Switching Losses vs. Collector Current



**Fig. 12** - Turn-Off SOA



**Fig. 13** - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

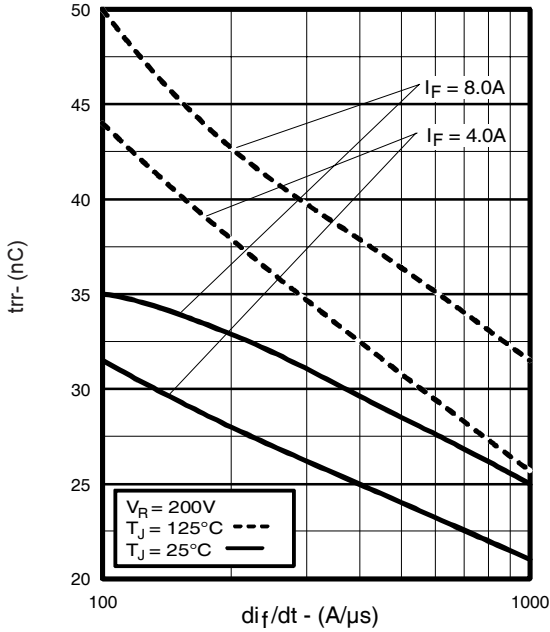


Fig. 14 - Typical Reverse Recovery vs.  $di_f/dt$

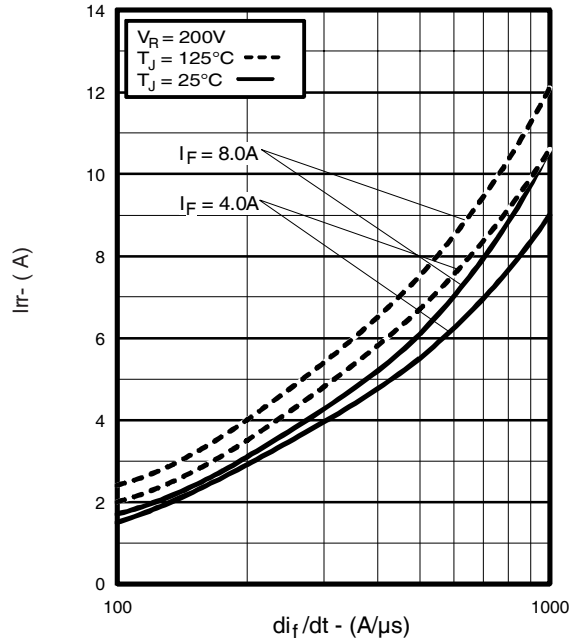


Fig. 15 - Typical Recovery Current vs.  $di_f/dt$

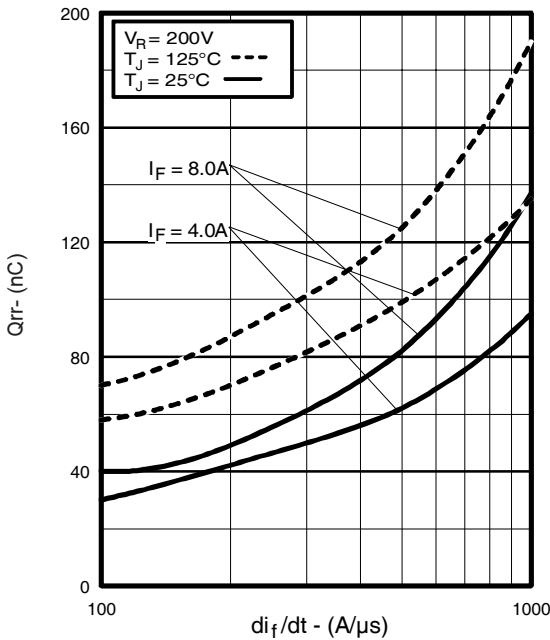


Fig. 16 - Typical Stored Charge vs.  $di_f/dt$

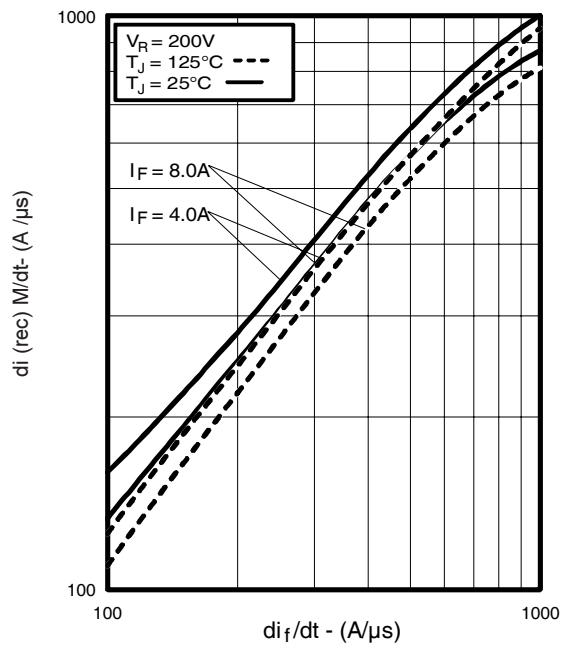
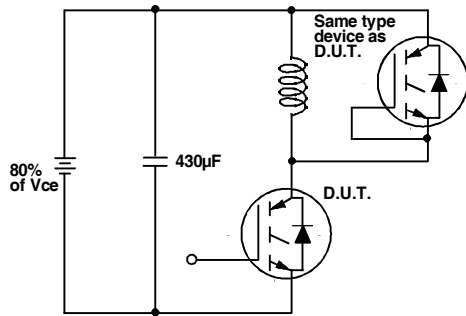
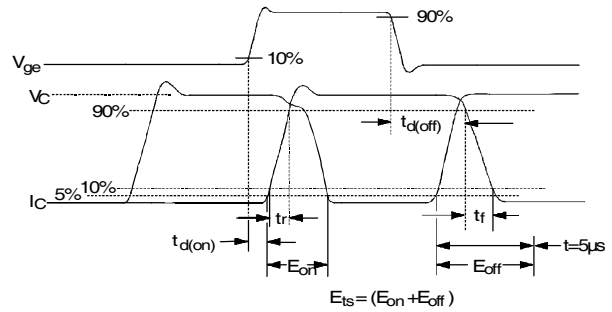


Fig. 17 - Typical  $di_{(rec)M}/dt$  vs.  $di_f/dt$

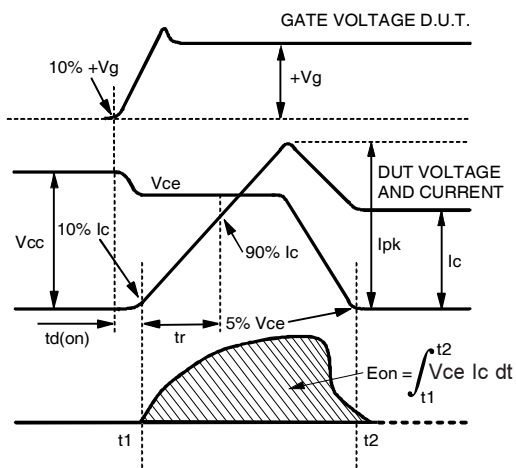
# IRG4BC10SD



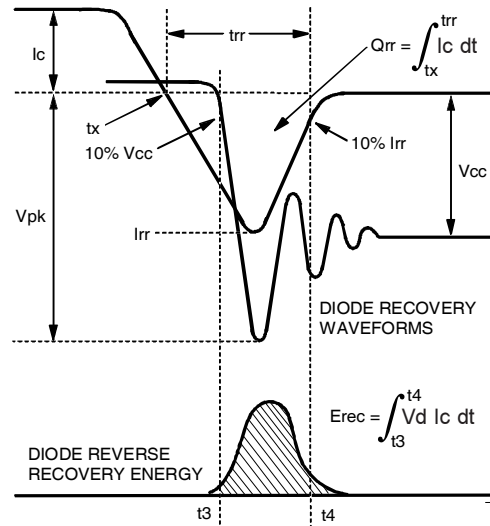
**Fig. 18a** - Test Circuit for Measurement of  $I_{LM}$ ,  $E_{on}$ ,  $E_{off}(\text{diode})$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$ ,  $t_{d(on)}$ ,  $t_r$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18b** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{off}$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18c** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{on}$ ,  $t_{d(on)}$ ,  $t_r$



**Fig. 18d** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{rec}$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$



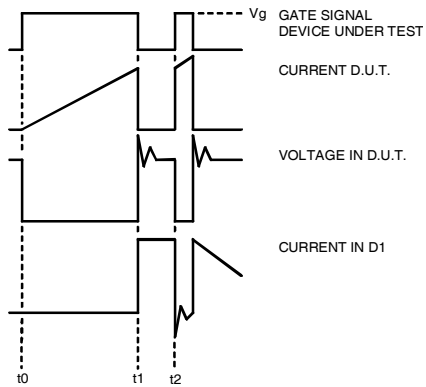


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

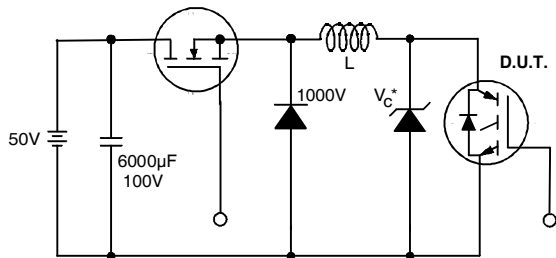


Figure 19. Clamped Inductive Load Test Circuit

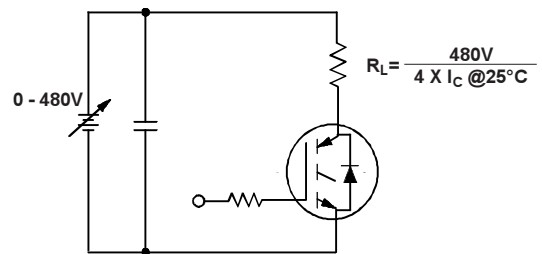


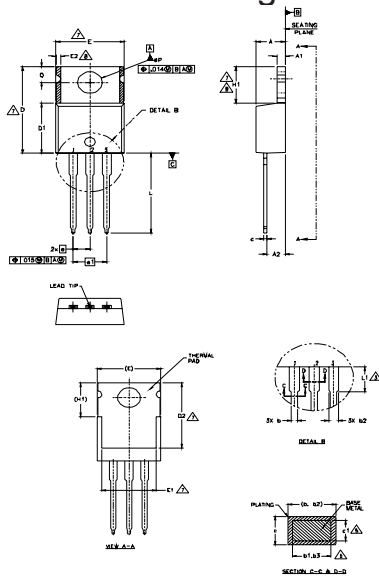
Figure 20. Pulsed Collector Current Test Circuit

# IRG4BC10SD

## Notes:

- ① Repetitive rating:  $V_{GE}=20V$ ; pulse width limited by maximum junction temperature (figure 20)
- ②  $V_{CC}=80\%(V_{CES})$ ,  $V_{GE}=20V$ ,  $L=10\mu H$ ,  $R_G = 100W$  (figure 19)
- ③ Pulse width  $\leq 80\mu s$ ; duty factor  $\leq 0.1\%$ .
- ④ Pulse width  $5.0\mu s$ , single shot.

## TO-220AB Package Outline (Dimensions are shown in millimeters (inches))



- NOTES:
- 1.- DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
  - 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
  - 3.- LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
  - 4.- DIMENSION D, D1 & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
  - 5.- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
  - 6.- CONTROLLING DIMENSION - INCHES.
  - 7.- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
  - 8.- DIMENSION E2 x H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.
  - 9.- OUTLINE CONFORMS TO JEDEC TO-220, EXCEPT A2 (max.) AND D2 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.03	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.97	.015	.038	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	11.68	12.88	.460	.507	7
E	9.65	10.67	.380	.420	4,7
E1	6.86	8.89	.270	.350	7
E2	-	0.76	-	.030	8
e	2.54 BSC		.100 BSC		
e1	5.08 BSC		.200 BSC		
H1	5.84	6.86	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	-	6.35	-	.250	3
RP	3.54	4.08	.139	.161	
O	2.54	3.42	.100	.135	

### LEAD ASSIGNMENTS

#### HEXKEET

- 1- GATE
- 2- DRAIN
- 3- SOURCE

#### ISBTL DgPACK

- 1- GATE
- 2- COLLECTOR
- 3- EMITTER

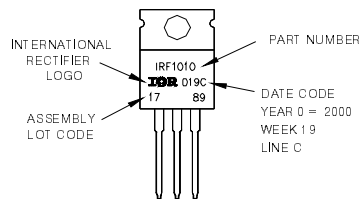
#### DIODES

- 1- ANODE/OPEN
- 2- CATHODE
- 3- ANODE

## TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010  
LOT CODE 1 789  
ASSEMBLED ON WW 19, 2000  
IN THE ASSEMBLY LINE 'C'

Note: 'P' in assembly line position  
indicates 'Lead - Free'



**Note:** For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Data and specifications subject to change without notice.